PUTs
Planar, TO-18 Hermetic

FEATURES
- Voltage Ratings: to 100V
- Maximum Peak Current: 150nA
- Valley Current: as low as 25 μA
- Low Forward Voltage Drop
- Nano-Amp Leakage
- Hermetically Sealed TO-18 Metal Can

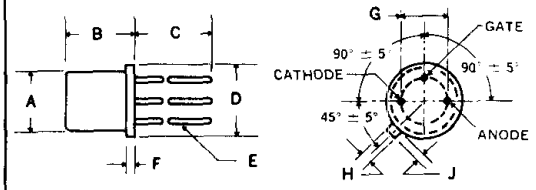
DESCRIPTION
The Unitrode hermetically sealed TO-18 metal can series of programmable unijunction transistors feature blocking voltages to 100V, the highest available to designers. These PUTs are functionally equivalent to standard unijunction transistors, with the added advantages of programming versatility. External resistors can be added to program η, R_{BB}, I_p and I_v, depending upon your design requirements. All units are fully planar passivated. This series features a hermetically sealed TO-18 package for optimum reliability in all environmental conditions. Applications include pulse and timing circuits, SCR trigger circuits, relaxation oscillators, and sensing circuits. For further application information see Unitrode's Application Note U-66.

ABSOLUTE MAXIMUM RATINGS

Anode-to-Cathode Forward Voltage, V_{AK}	40V
Anode-to-Cathode Reverse Voltage, V_{AKR}	40V
Gate-to-Cathode Forward Voltage, V_{GK}	40V
Gate-to-Anode Reverse Voltage, V_{GAR}	40V
Gate-to-Cathode Reverse Voltage, V_{GKR}	5V
Peak Recurrent Forward Current	
10 μs 1% Duty Cycle	8A
100 μs 1% Duty Cycle	5A
Power Dissipation	
25°C Ambient	400mW
Derating Factor	3.2mW/°C
Storage Temperature Range	−55°C to +150°C
Operating Temperature Range	−55°C to +150°C

MECHANICAL SPECIFICATIONS

U13T1-U13T2



GATE CONNECTED TO CASE

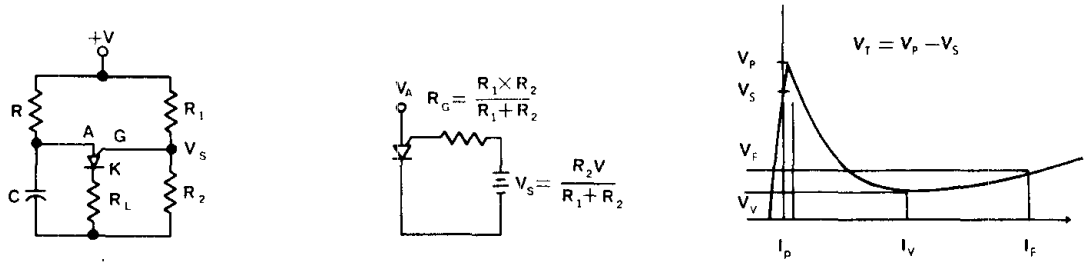
	INCHES	MILLIMETERS
A	.178–.195 DIA.	4.52–4.95 DIA.
B	.170–.210	4.31–5.33
C	.5 MIN.	12.70 MIN.
D	.209–.230 DIA.	5.31–5.84 DIA.
E	.017 ± .002 DIA. .001 DIA.	.432 ± .051 .025
F	.020 MAX.	.508 MAX.
G	.100±.010 DIA.	2.54±.254 DIA.
H	.041±.005	1.04±.127
J	.028–.048	.711–1.22

TO-18

UNITRODE

ELECTRICAL SPECIFICATIONS (at 25°C unless noted)

Test	Symbol	Fig.	U13T1 Min.	U13T1 Max.	U13T2 Min.	U13T2 Max.	Units	Test Conditions
Peak Current	I_P	1	— —	5 2	— —	1.0 0.15	μA μA	$R_G = 10k, V_s = 10V$ $R_G = 1$ Meg.
Valley Current	I_V	1	70 —	— 50	25 —	— 25	μA μA	$R_G = 10k, V_s = 10V$ $R_G = 1$ Meg.
Offset Voltage	V_T	1	0.2 0.2	0.6 1.6	0.2 0.2	0.6 0.6	V V	$R_G = 10k, V_s = 10V$ $R_G = 1$ Meg.
Gate-to-Anode Leakage	I_{GAO}	2	— —	10 100	— —	10 100	nA nA	$T = 25°C, V_s$ = rating $T = 75°C$
Gate-to-Cathode Leakage	I_{GKS}	3	—	100	—	100	nA	V_s = rating
Forward Voltage	V_F	4	—	1.5	—	1.5	V	$I_F = 50mA$
Pulse Output Voltage	V_o	5	6	—	6	—	V	
Pulse Output Rate of Rise	t_r	5	—	80	—	80	n[illegible]	



a) Typical Circuit b) Equivalent Test Circuit c) Characteristic Curve

Figure 1

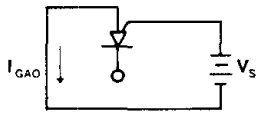


Figure 2

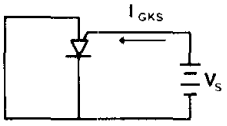


Figure 3

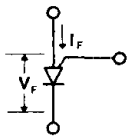


Figure 4

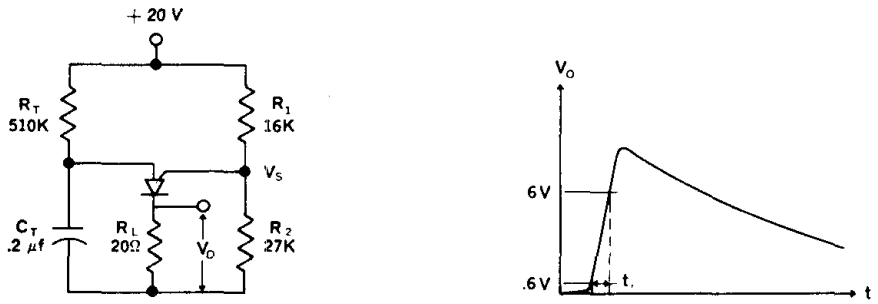


Figure 5